EE210: Microelectronics-I

Lecture-6 : PN Junction Diode-2

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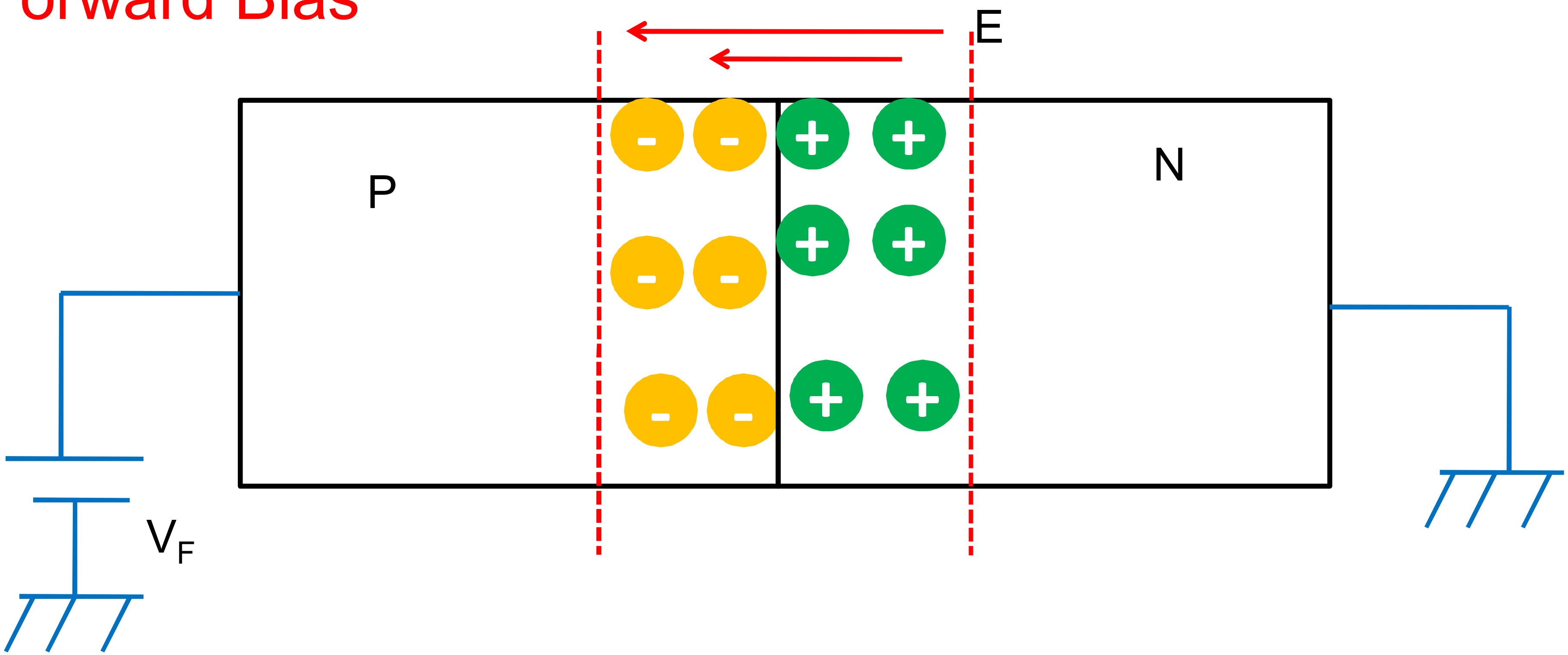
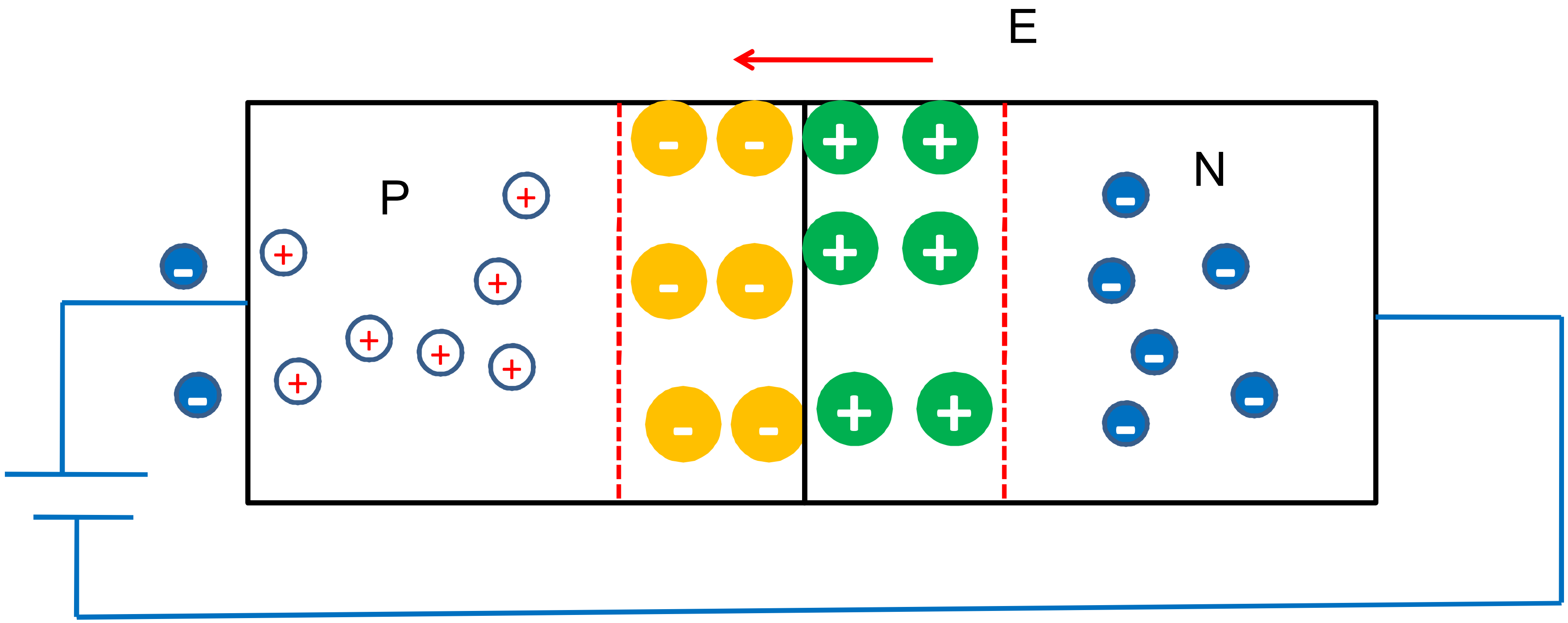
Forward Bias



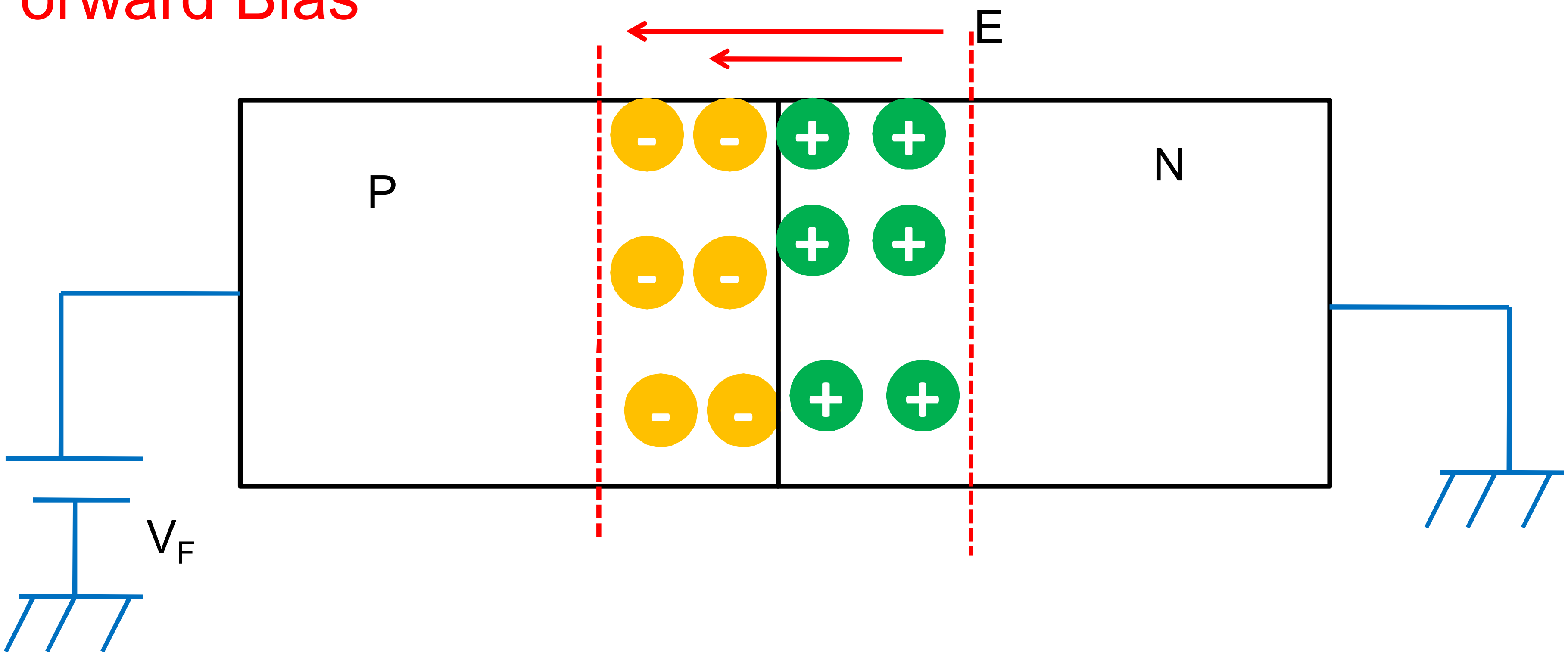
Application of forward bias reduces electric field and depletion width.

Mechanism of Current flow



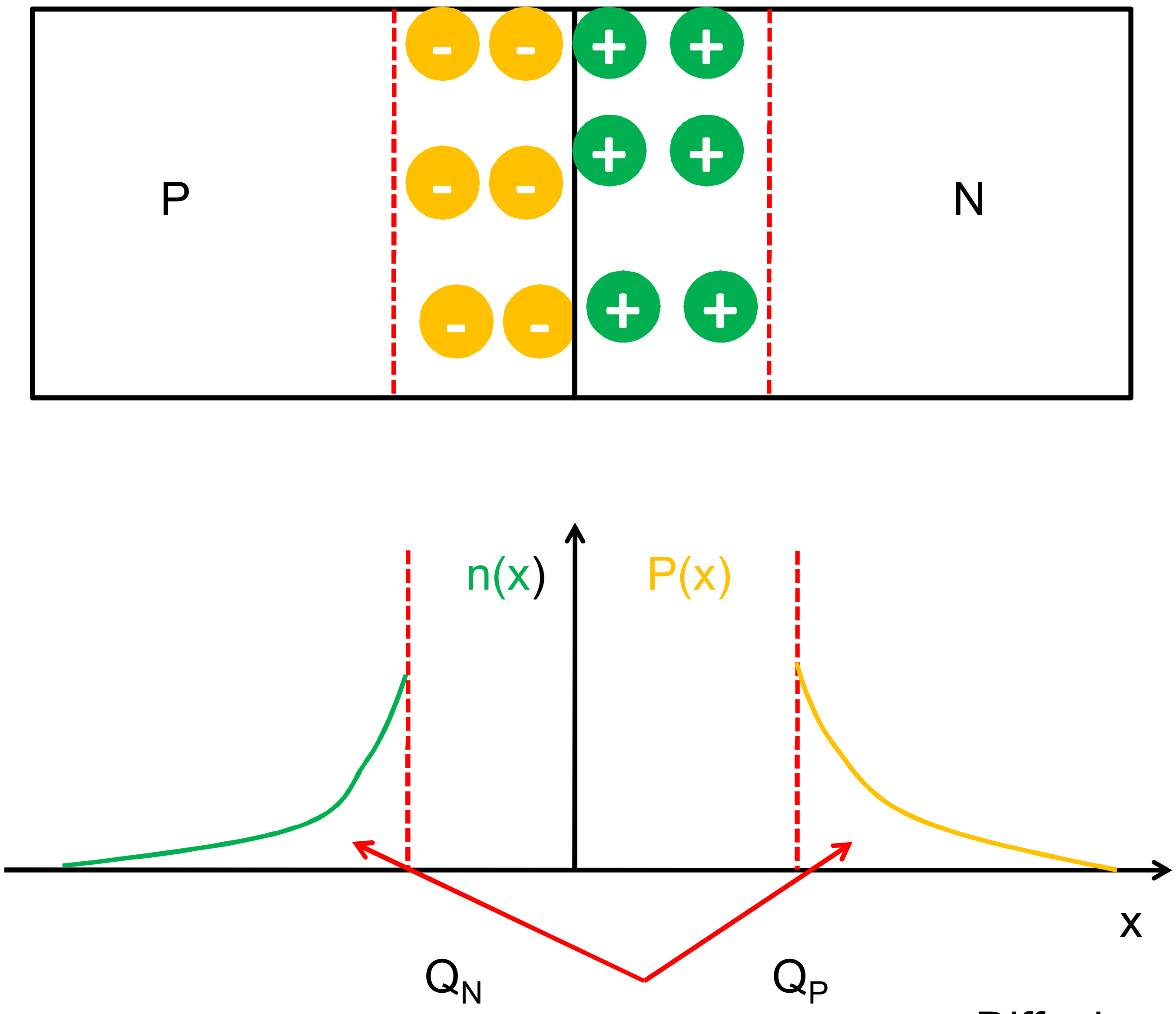
Current flows through carrier **injection** and **recombination**

Forward Bias



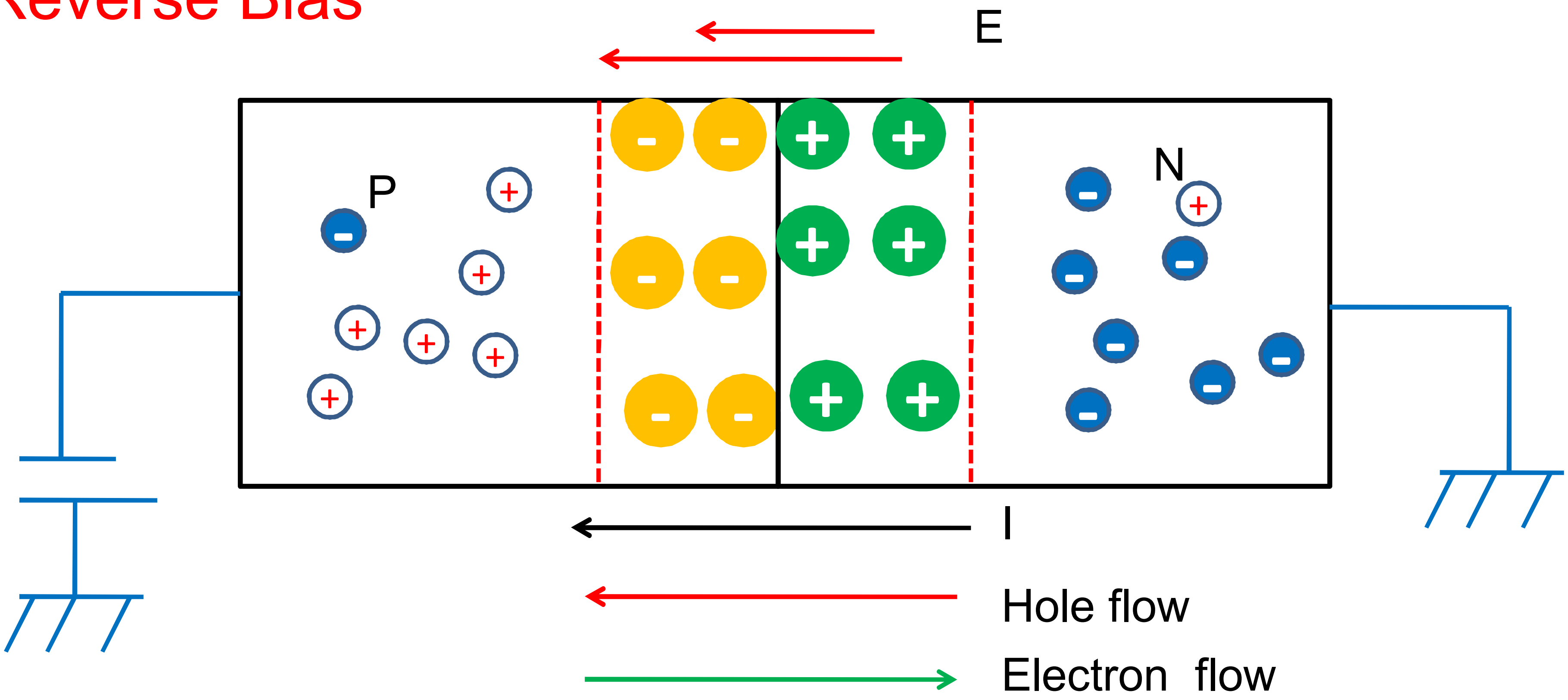
Change in depletion charge with voltage gives rise to junction capacitance (also called depletion capacitance) C_J

Excess carriers in P and N regions



Diffusion capacitance

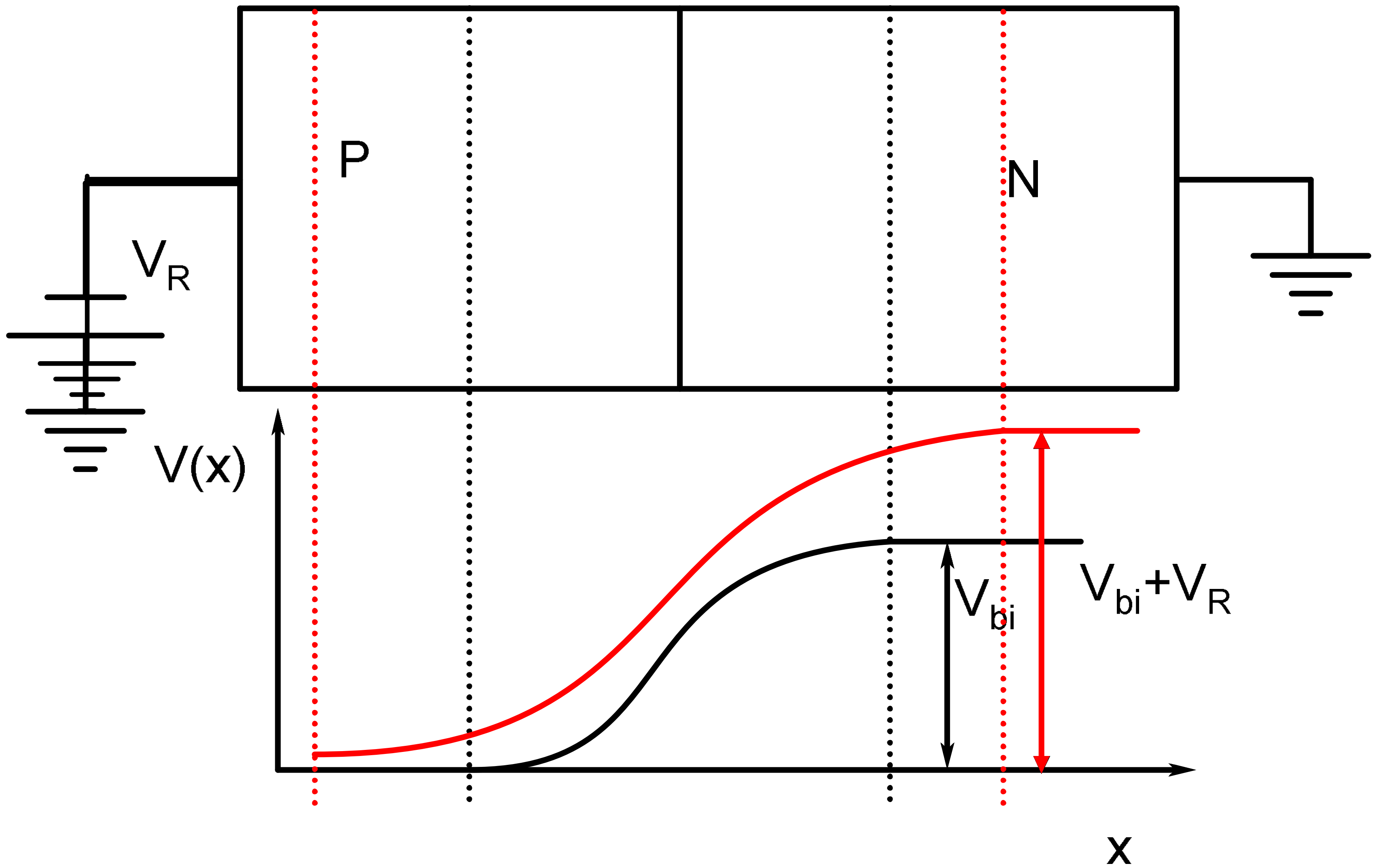
Reverse Bias



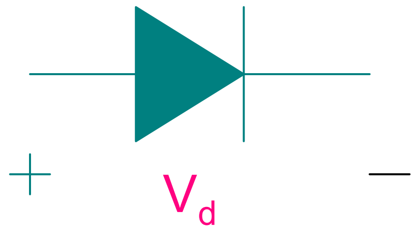
Because of very few electrons in p-type and holes in N-type current is very small !

Application of reverse bias increases the built-in potential

Reverse Bias



Diode : I-V Characteristics



$$I = I_S \times \left(\exp\left(\frac{V_D}{nV_T}\right) - 1 \right)$$

I_S : Reverse Saturation Current

$V_T = kT/q \cong 26mV$ at T = 300K

n is called ideality factor and is equal to 1 for ideal diodes

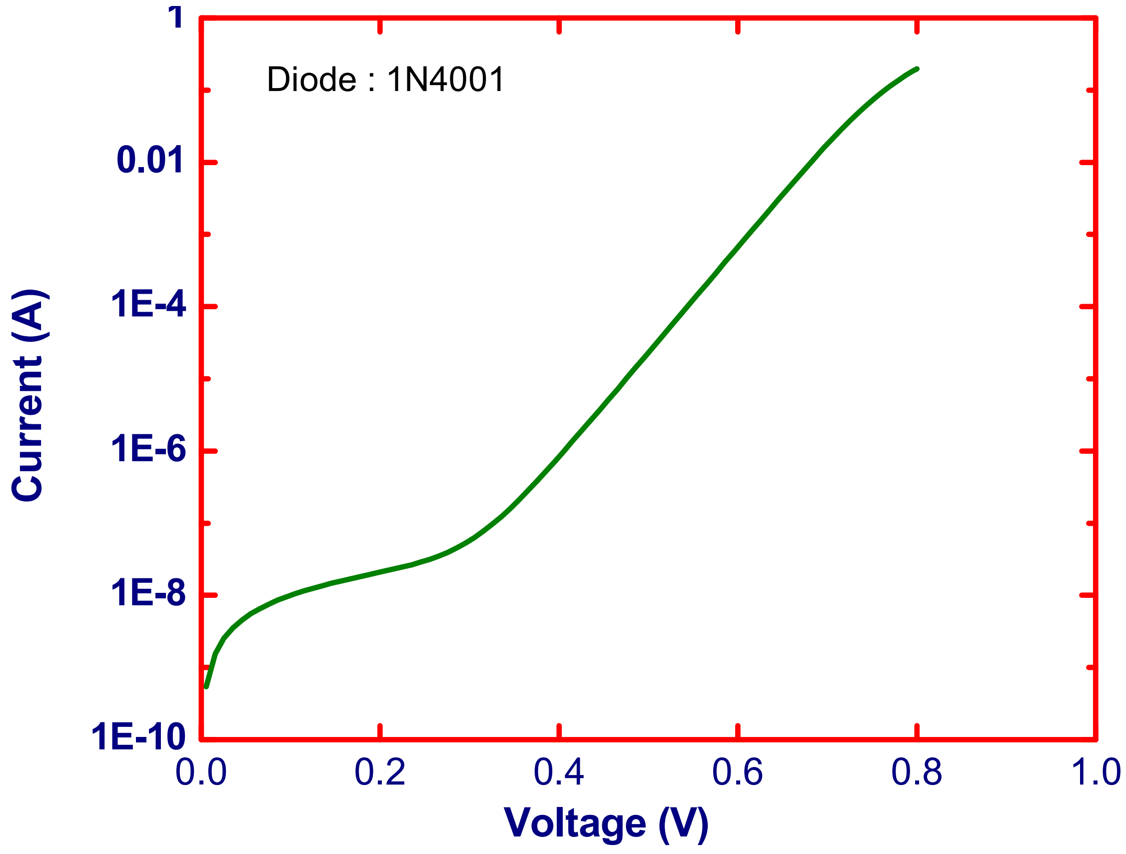
Forward Bias

$$I = I_S \times \left(\exp\left(\frac{V_d}{V_T}\right) - 1 \right)$$

$$V_d >> V_T = 26mV$$

$$I \cong I_S \times \exp\left(\frac{V_d}{V_T}\right)$$

$$\ln(I) = \ln(I_S) + \frac{V_d}{V_T}$$

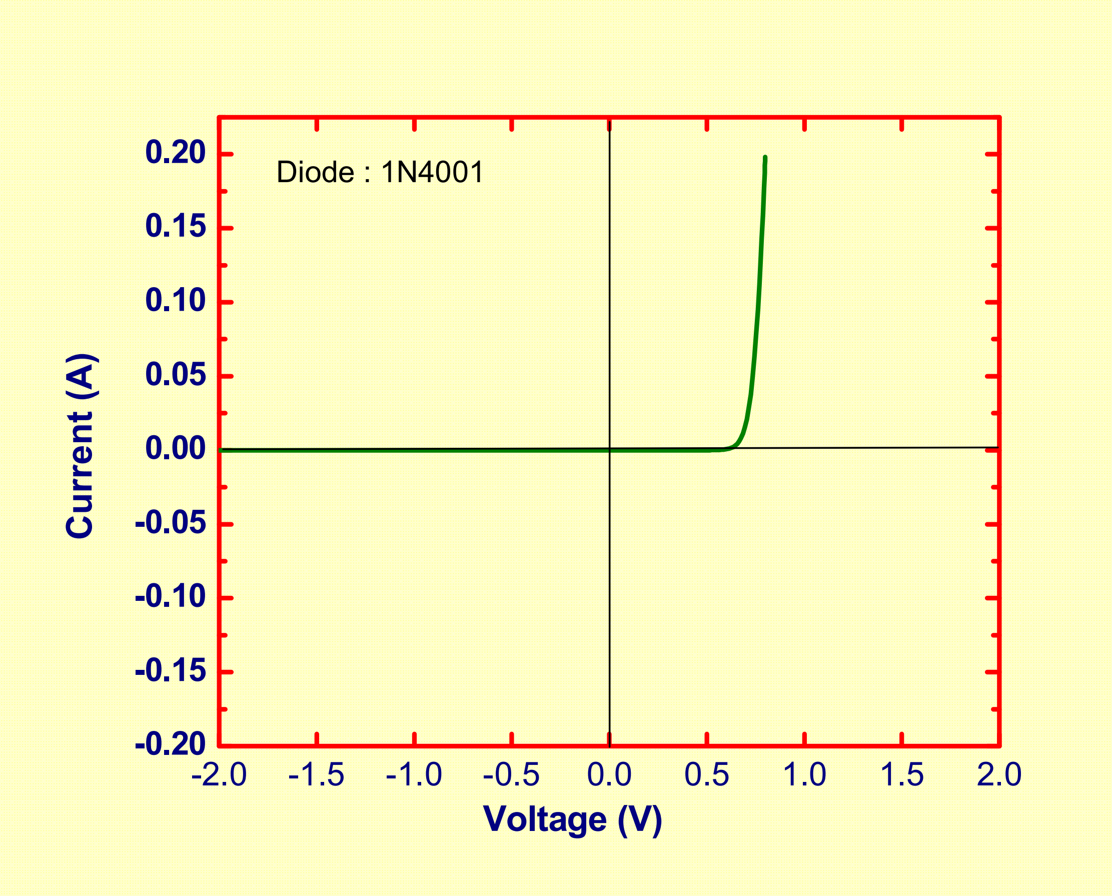


Reverse Bias

$$I = I_S \times \left(\exp\left(\frac{V_d}{V_T}\right) - 1 \right)$$

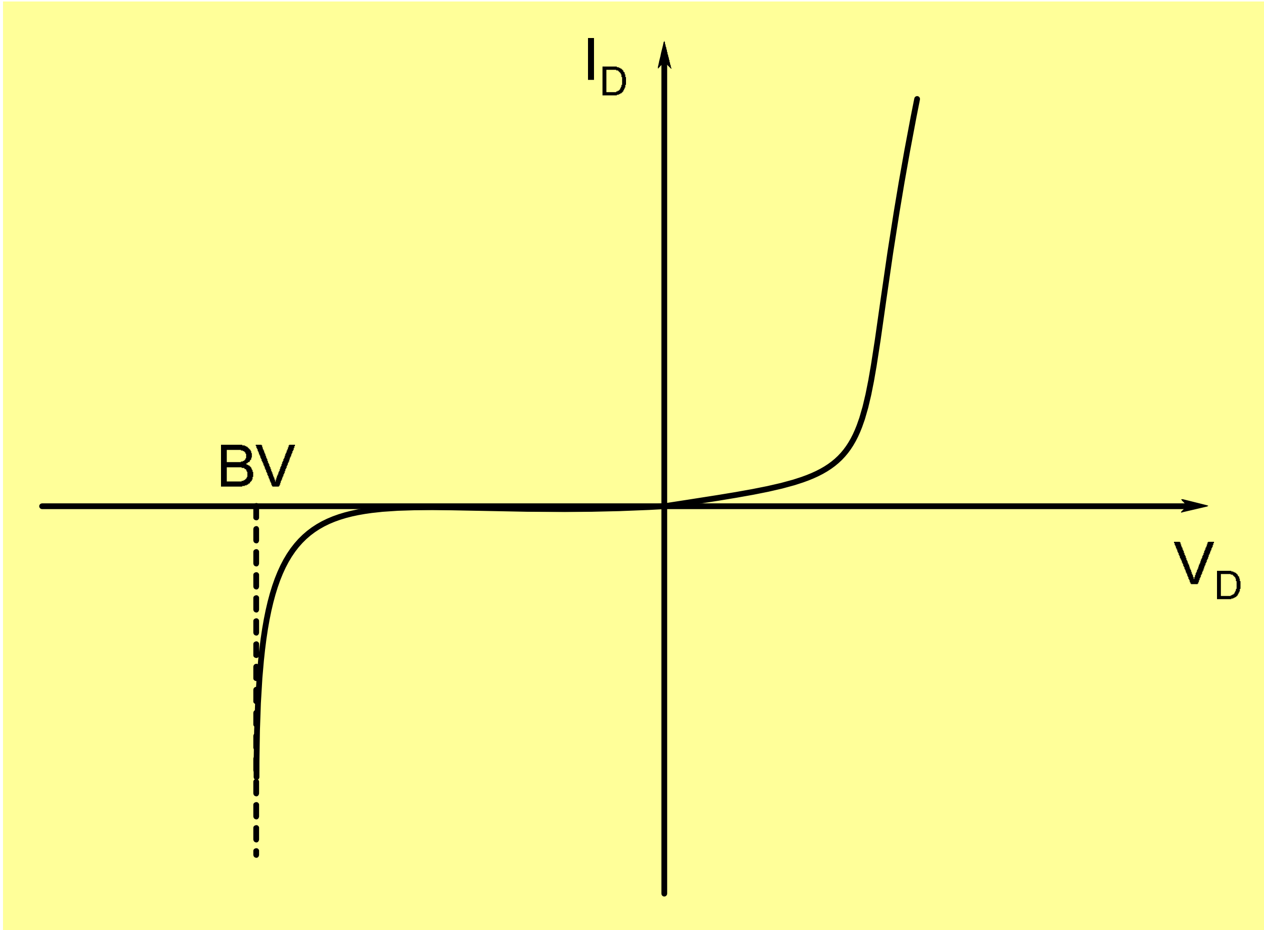
$$V_d = -V_R$$

$$I = I_S \times \left\{ \exp\left(-\frac{V_R}{V_T}\right) - 1 \right\} \cong -I_S$$

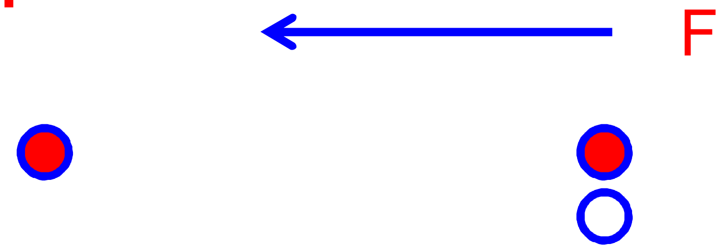


Reverse current may be much higher than I_S

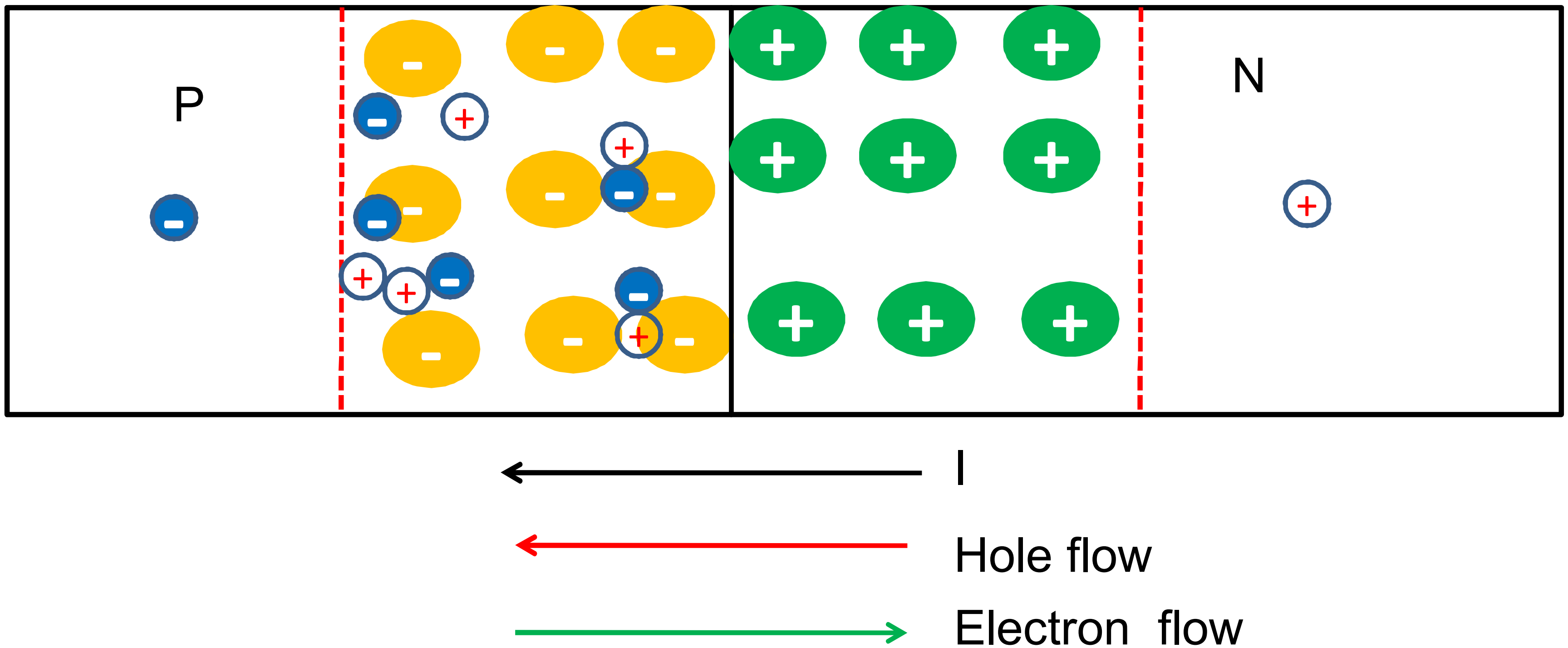
Breakdown



Impact Ionization



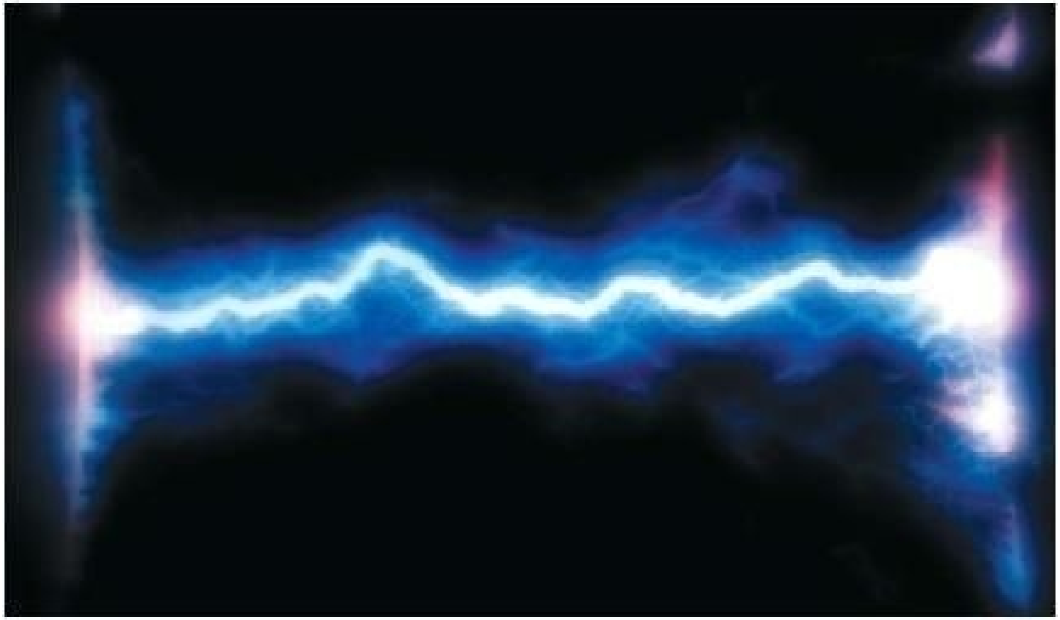
Breakdown Mechanism: Avalanche



A multiplication of carriers takes place due to impact ionization in the depletion region, as a result of which large current begins to flow.

Avalanche

Zener Breakdown Heavily doped junctions



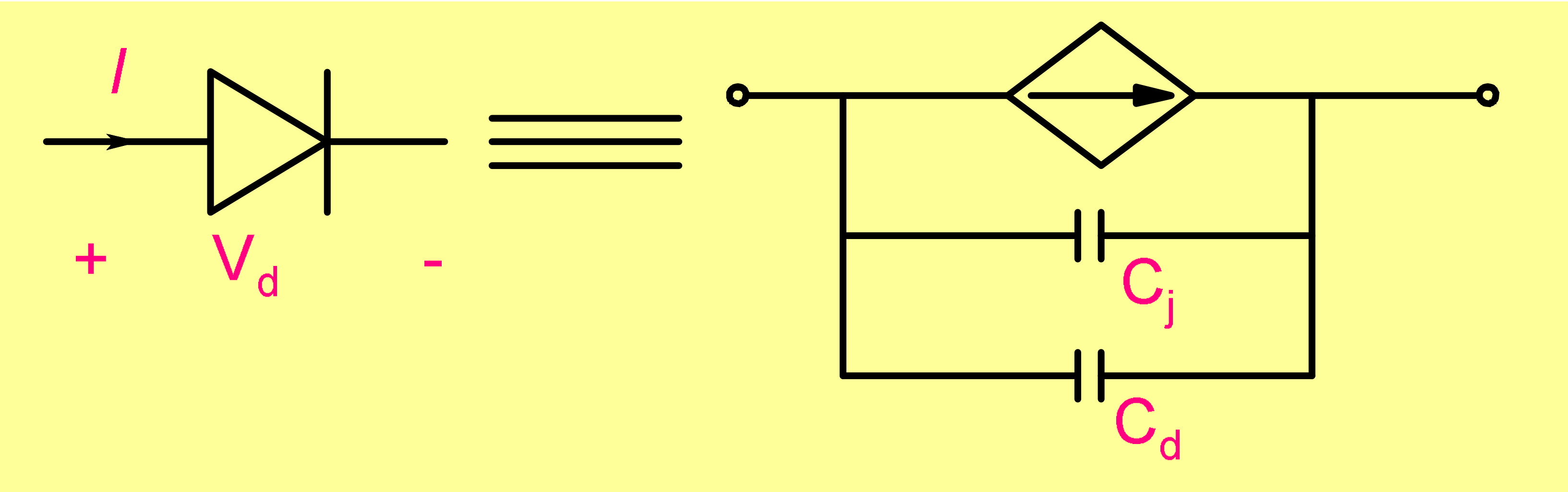
Electric Arc

Electric field "**breaks the bond"** creating electron and hole pairs. These carriers move to give rise to large current.

In most of the common pn junction diodes breakdown occurs due to avalanche mechanism. Even diodes which are called zener diodes have avalanche breakdown

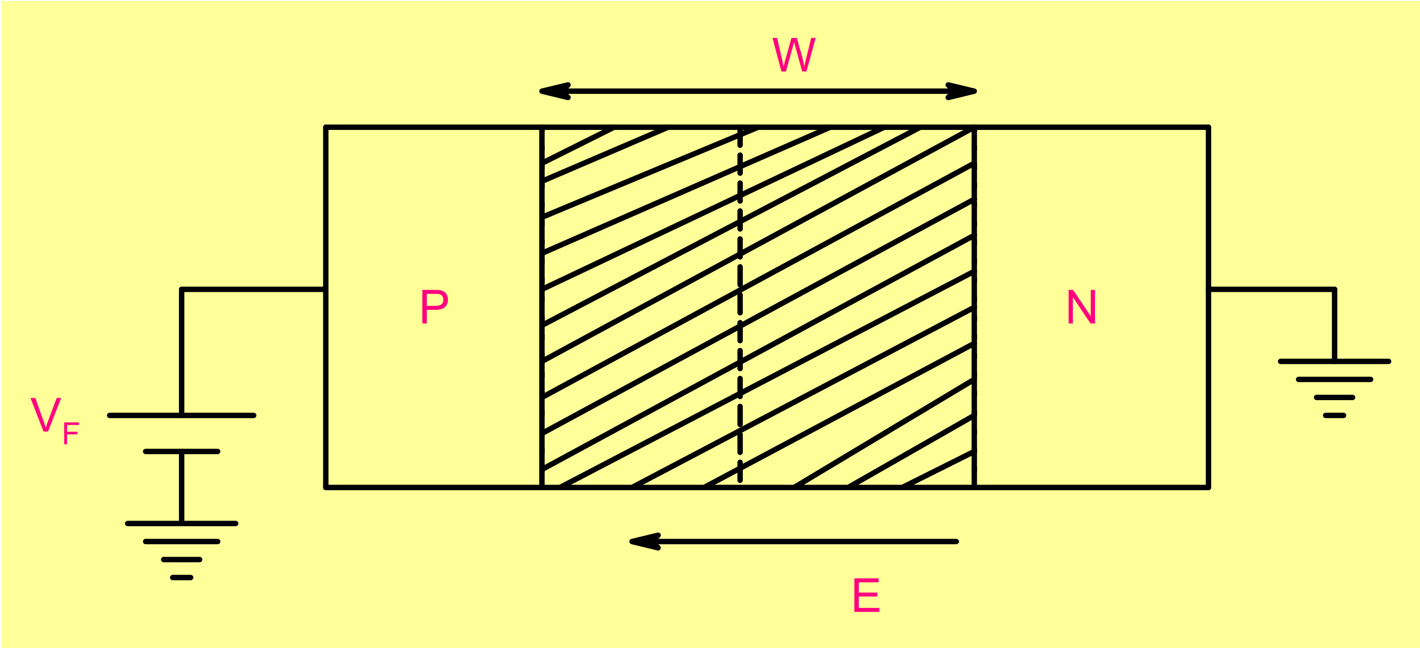
Diode Model: Forward Bias

$$I = I_S \times \left(\exp\left(\frac{V_d}{nV_T}\right) - 1 \right)$$



For dc and low frequency ac circuits, the effect of diode capacitance can be neglected

Junction Capacitance



$(\uparrow)\ V_F \longrightarrow E(\downarrow) \longrightarrow Q_j\ (\downarrow)$

$$C_j = -\frac{\partial Q_j}{\partial V_F}$$

$$C_j = \frac{\varepsilon_s}{W} \times Area$$

$$C_j = \frac{C_{j0}}{\left(1 - \frac{V_d}{V_{bi}}\right)^m}$$

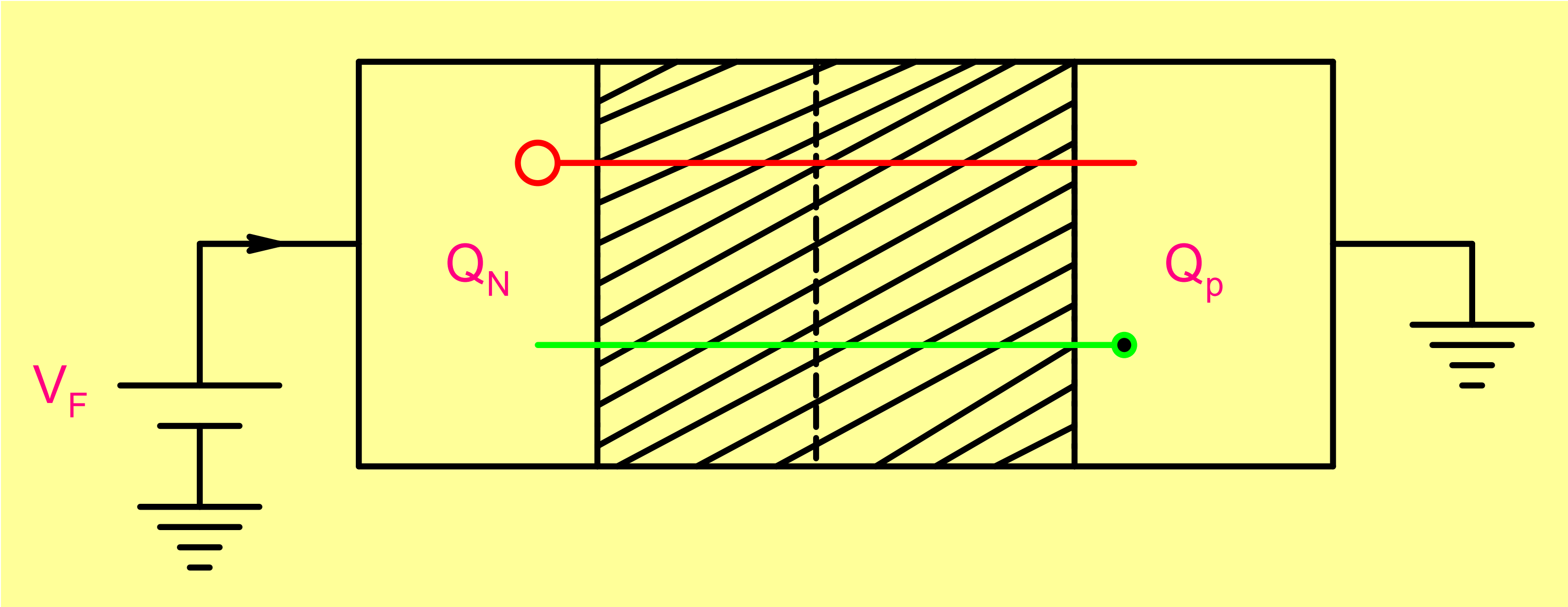
C_{jo} : Zero bias junction Capacitance

V_{bi} : built-in potential

m : grading coefficient (~ 0.5, 0.33)

- Junction capacitance increases with forward bias
- Junction capacitance increases with doping
- Junction capacitance increases with Area

Diffusion Capacitance

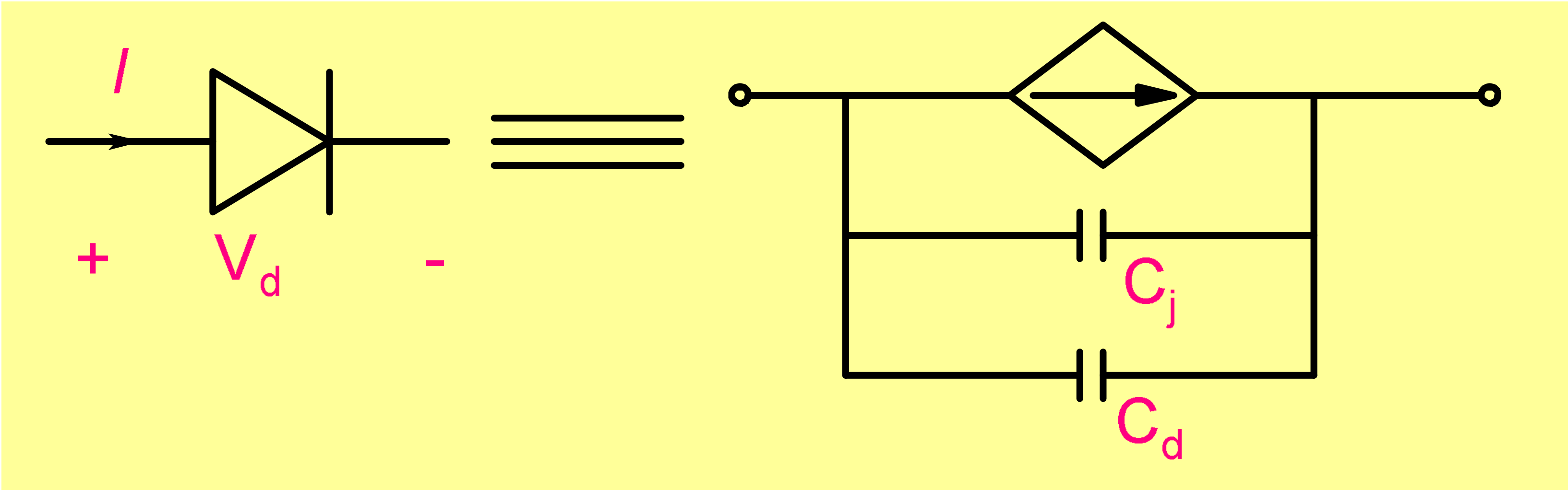


$$C_d = \frac{\partial\left(Q_P + |Q_N|\right)}{\partial V_F}$$

$$C_d = \frac{I_F}{V_T} \cdot \tau$$

τ : transit time

Diode Model: Forward Bias



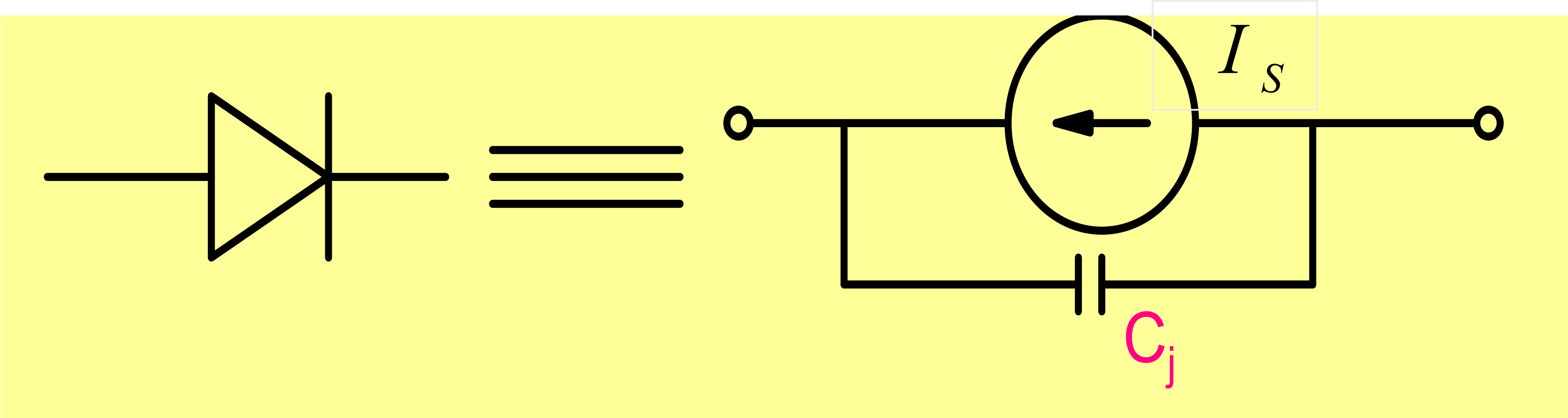
$$I = I_S \times \left(\exp\left(\frac{V_d}{nV_T}\right) - 1 \right)$$

$$C_j = \frac{C_{j0}}{\left(1 - \frac{V_d}{V_{bi}}\right)^m}$$

$$C_d = \frac{I_F}{V_T} \cdot \tau$$

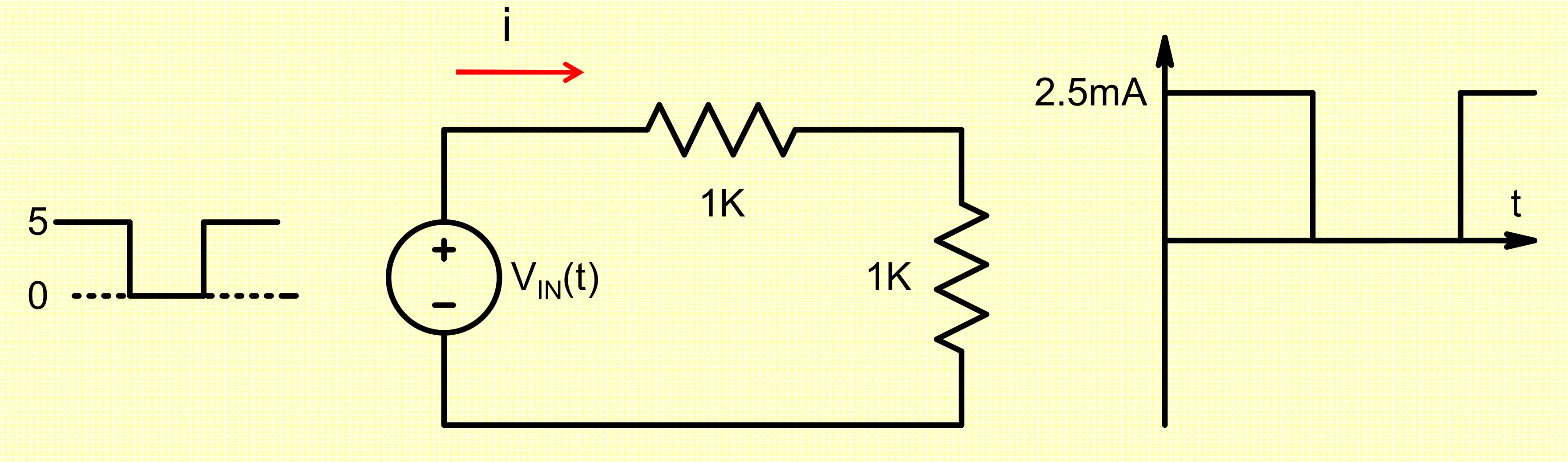
No. of parameters: 3+3+1

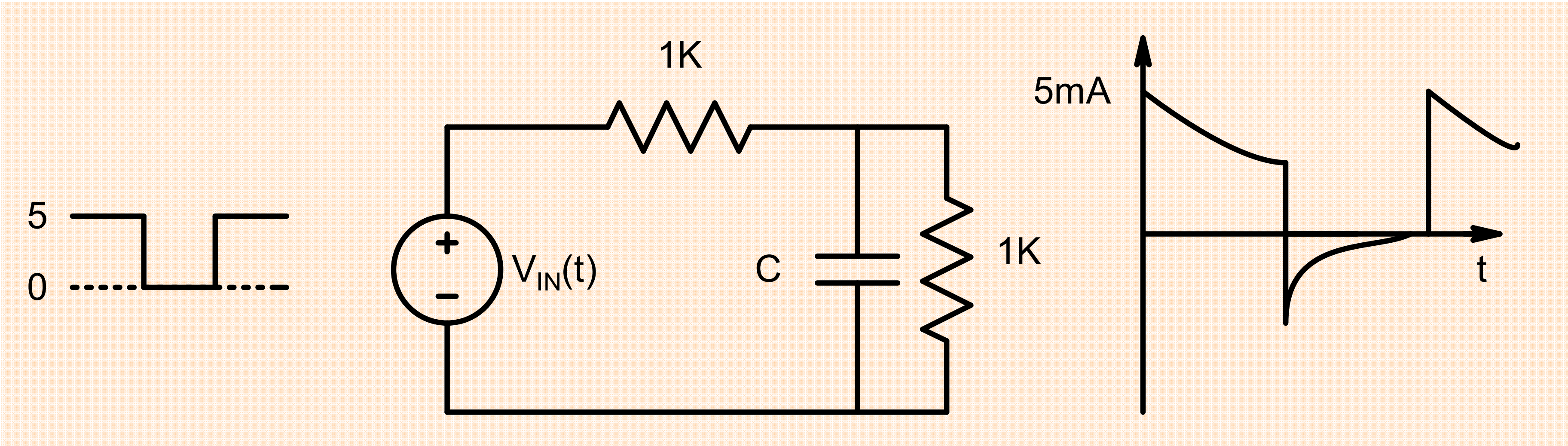
Diode Model: Reverse Bias

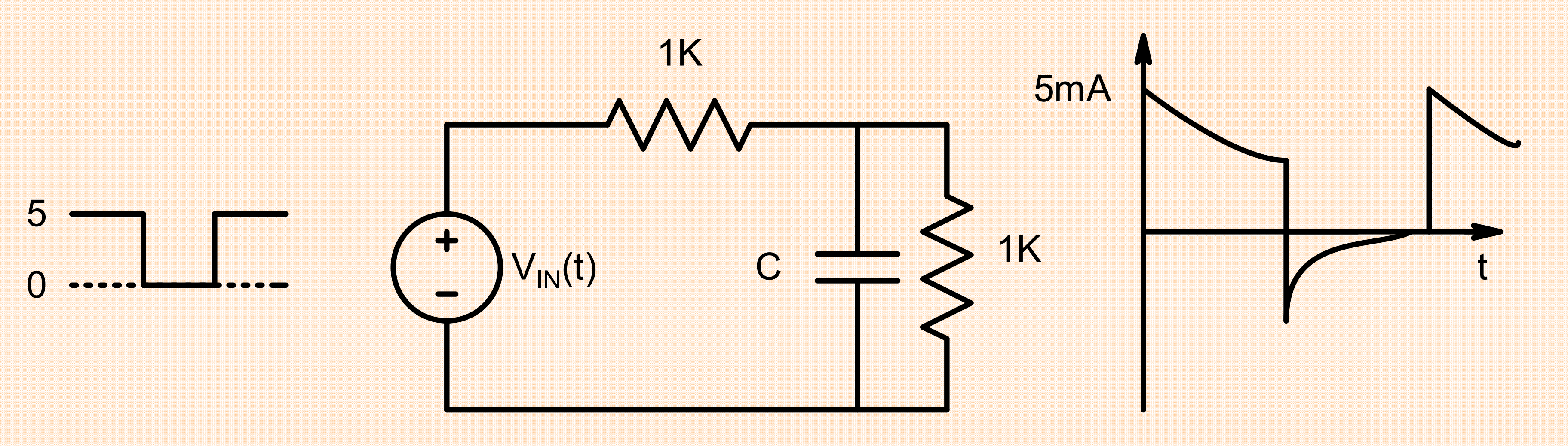


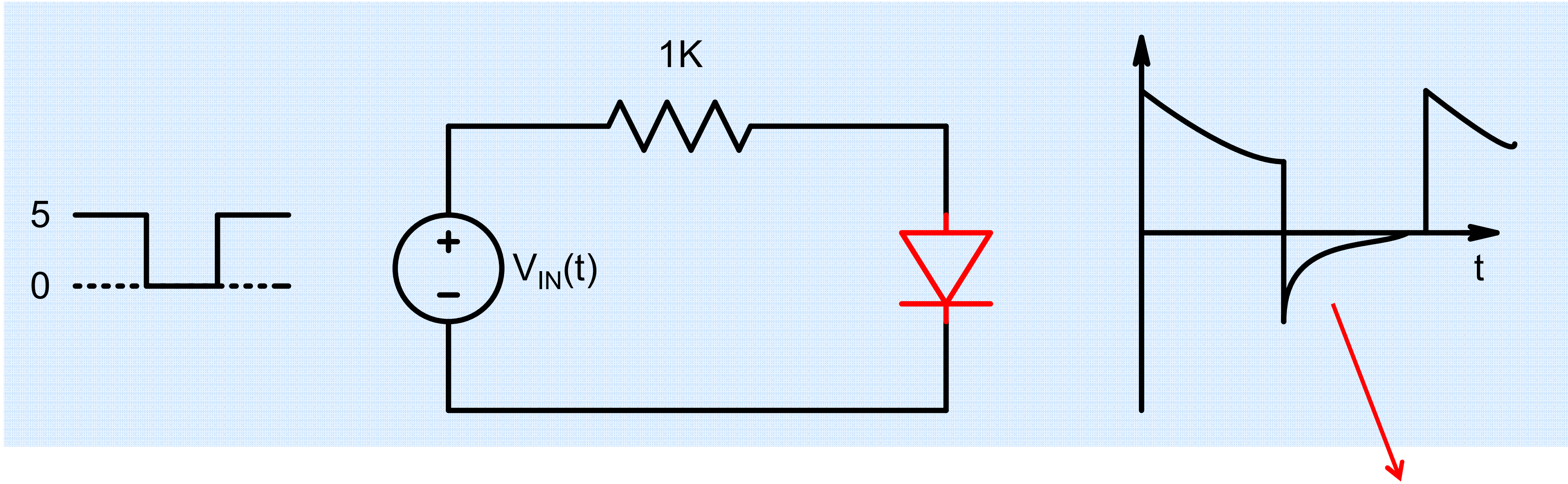
Because of capacitance, a diode even though reverse biased, can carry significant current momentarily

Example



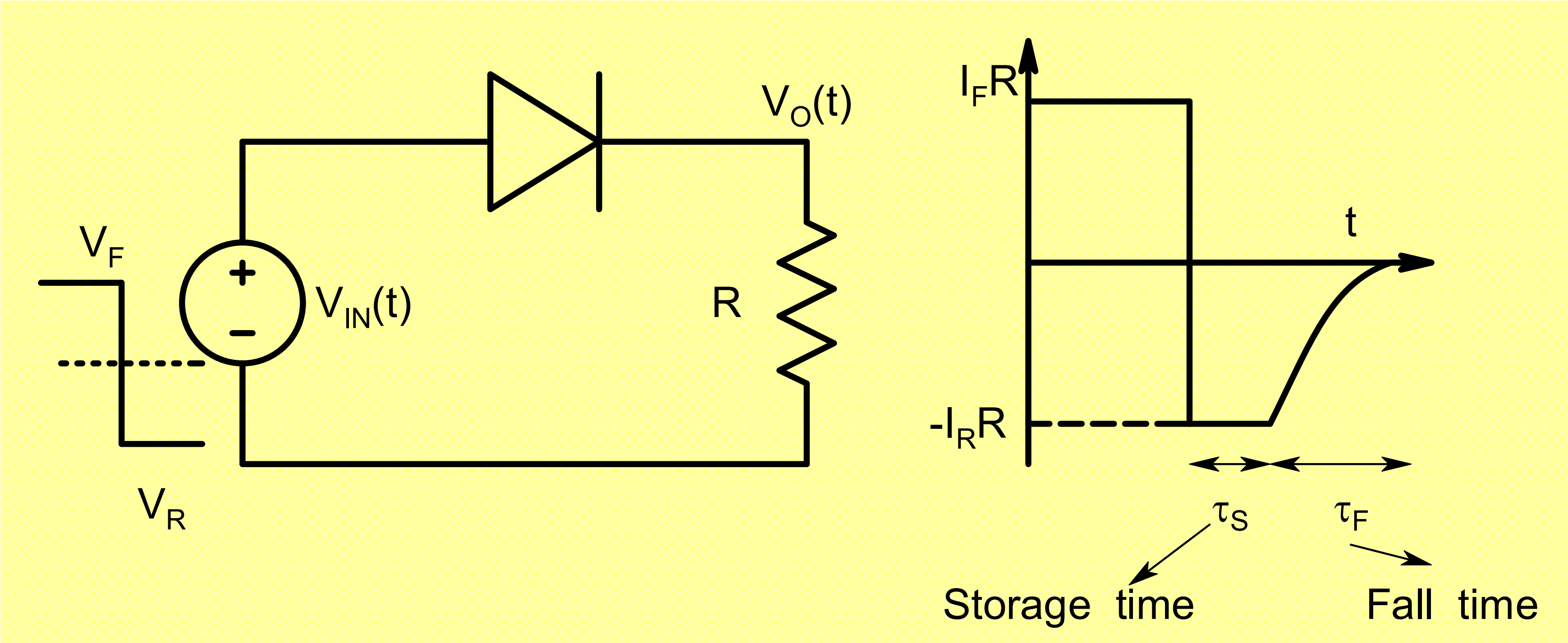






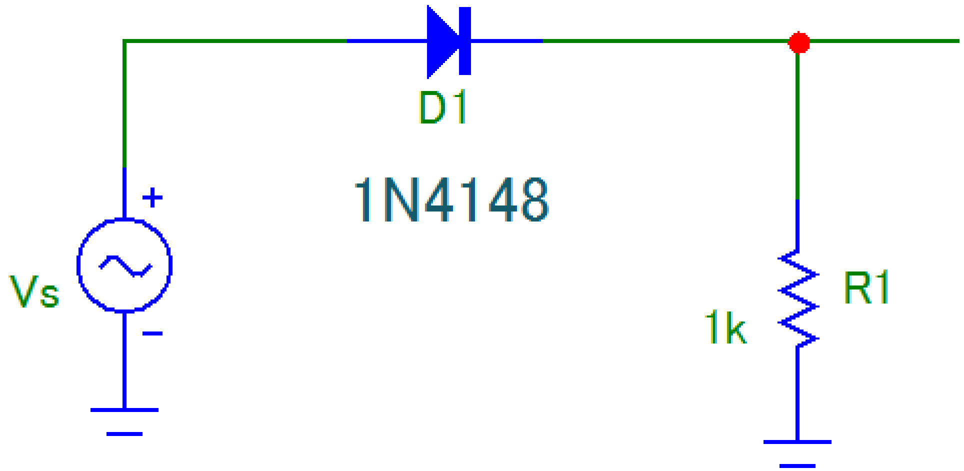
Current in reverse direction

Transient Response

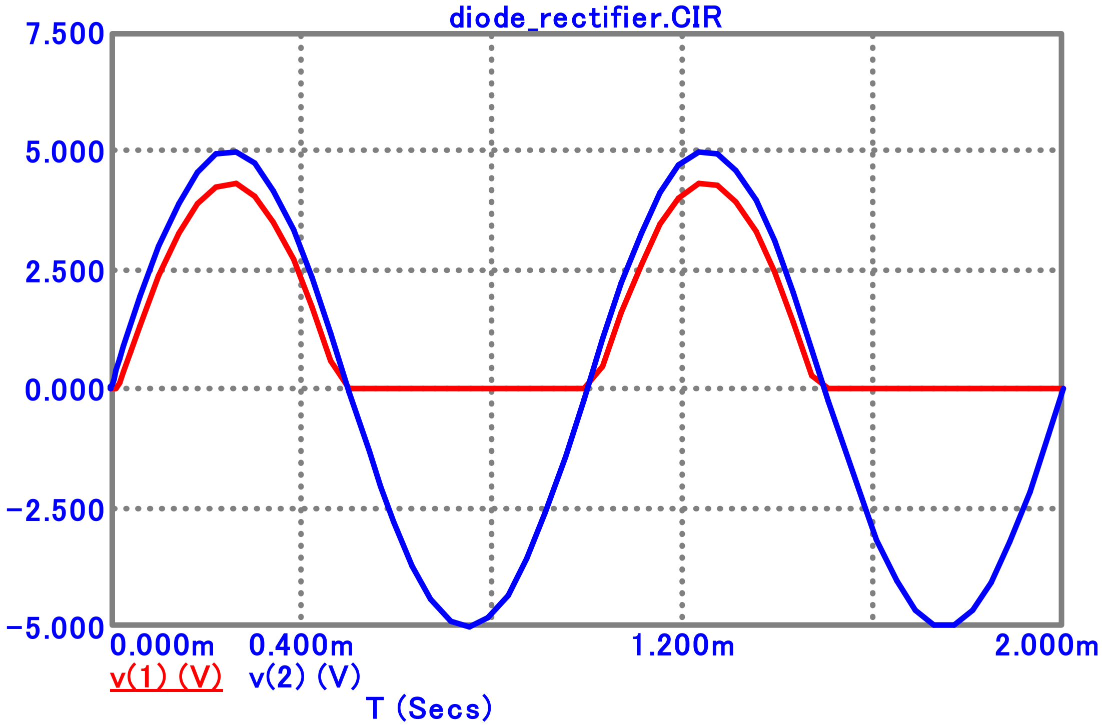


Diode does not switch off instantly but remains conducting for a period called reverse recovery time which is sum of storage and fall delay times..

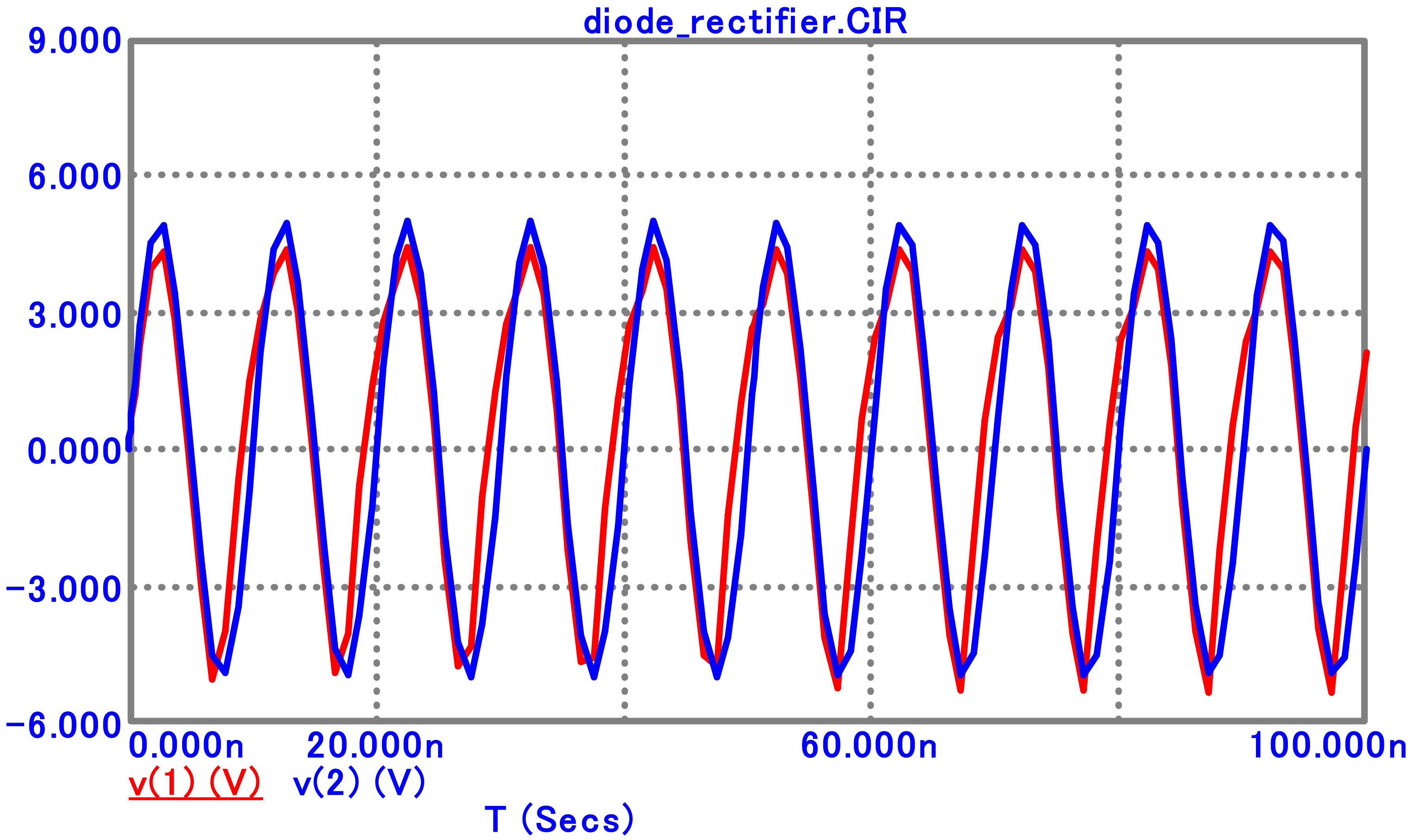
Rectifier



F = 1 kHz



F = 100 MHz



diode_rectifier.CIR
9.000
6.000
3.000
0.000
−3.000
−6.000
0.000n
20.000n
60.000n
100.000n
v(1) (V)
v(2) (V)
T (Secs)